



# **PRODUCT DATA SHEET**



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Datasheet

ources Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO\_questions@jgsemi.com.

**ESD Protection Diode** 

#### **Features**

- 200Watts peak pulse power (tp =  $8/20\mu$ s)
- SOD523 package
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=75pF typ.)
- Protection one data/power line to:
- IEC 61000-4-2 ±30kV contact ±30kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 11A (8/20μs)

## **Applications**

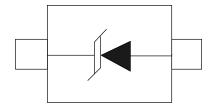
- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation

### **Mechanical Data**

- SOD523 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant



**SOD-523** 





**Absolute Maximum Rating** 

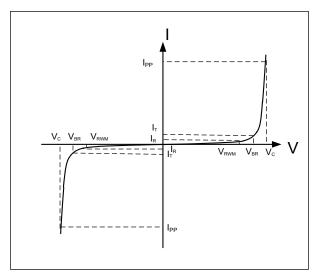
Rating	Symbol	Value	Units	
Peak Pulse Power ( $t_p = 8/20 \mu s$ )	$P_{PP}$	200	Watts	
Peak Pulse Current ( $t_p = 8/20 \mu s$ ) (note1)	${ m I}_{ m pp}$	11	A	
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V <sub>ESD</sub>	30 30	kV	
Lead Soldering Temperature	$T_{ m L}$	260(10seconds)	$^{\circ}$ C	
Junction Temperature	$T_{\mathrm{J}}$	-55 to + 125	$^{\circ}$ C	
Storage Temperature	$T_{ m stg}$	-55 to + 125	$^{\circ}$ C	

## **Electrical Characteristics**

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	$V_{RWM}$				5.0	V
Reverse Breakdown Voltage	$V_{BR}$	I <sub>T</sub> =1mA	6.0			V
Reverse Leakage Current	$I_R$	V <sub>RWM</sub> =5V,T=25°C			1.0	μΑ
Peak Pulse Current	$I_{PP}$	tp =8/20μs			11	A
Clamping Voltage	$V_{\rm C}$	$I_{PP}=11A, t_p=8/20 \mu s$			20	V
Junction Capacitance	C <sub>j</sub>	$V_R = 0V$ , $f = 1MHz$		75		pF

# **Electrical Parameters (TA = 25 °C unless otherwise noted)**

Symbol	Parameter		
$\mathbf{I}_{ ext{PP}}$	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ Ipp		
V <sub>RWM</sub>	Working Peak Reverse Voltage		
IR	Maximum Reverse Leakage Current @ VRWM		
$V_{\text{BR}}$	Breakdown Voltage @ IT		
Iτ	Test Current		



Note:.  $8/20\mu s$  pulse waveform.



## **Typical Characteristics**

Figure 1: Peak Pulse Power vs. Pulse Time

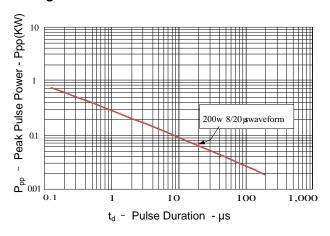


Figure 2: Power Derating Curve

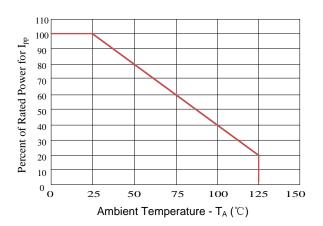


Figure3: Pulse Waveform

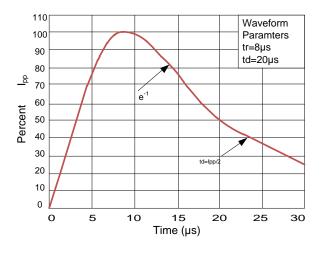
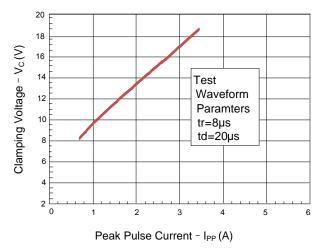
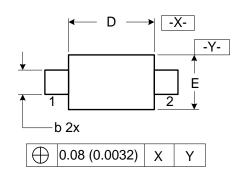


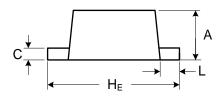
Figure 4: Clamping Voltage vs.lpp





## **Outline Drawing - SOD523**





#### **DIMENSIONS**

SYMBOL	MILLIMETER		INCHES		
	MIN	MAX	MIN	MAX	
Α	0.50	0.70	0.020	0.028	
b	0.25	0.35	0.010	0.014	
С	0.07	0.20	0.0028	0.0079	
D	1.10	1.30	0.043	0.051	
Е	0.70	0.90	0.028	0.035	
HE	1.50	1.70	0.059	0.067	
L	0.15	0.25	0.006	0.010	



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